

BC557AP Transistors

Si PNP Lo-Pwr BJT

Military/High-Rel N

V(BR)CEO (V) 45è

V(BR)CBO (V) 50

I(C) Max. (A) 100m

Absolute Max. Power Diss. (W) 500m

Maximum Operating Temp (øC) 150ö

I(CBO) Max. (A) 15nØ

@V(CBO) (V) (Test Condition)

V(CE)sat Max. (V)

@I(C) (A) (Test Condition)

@I(B) (A) (Test Condition)

h(FE) Min. Current gain. 120

h(FE) Max. Current gain.

@I(C) (A) (Test Condition) 100m

@V(CE) (V) (Test Condition) 5.0

f(T) Min. (Hz) Transition Freq 150M

@I(C) (A) (Test Condition)

@V(CE) (V) (Test Condition)

C(obo) (Max) (F) 4.5p

@V(CB) (V) (Test Condition)

@Fred. (Hz) (Test Condition)